

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

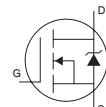
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.023	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.0	3.3	mΩ	$V_{GS} = 10V, I_D = 20A$ ③
		—	3.7	4.5		$V_{GS} = 4.5V, I_D = 16A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	—	2.35	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.4	—	mV/°C	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	87	—	—	S	$V_{DS} = 15V, I_D = 16A$
Q_g	Total Gate Charge	—	30	45	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 16A$ See Figs. 15 & 16
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	7.5	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	3.1	—		
Q_{gd}	Gate-to-Drain Charge	—	9.8	—		
Q_{godr}	Gate Charge Overdrive	—	9.6	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	12.9	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
Q_{oss}	Output Charge	—	18	—		
R_g	Gate Resistance	—	1.0	1.6	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ $I_D = 16A$ $R_G = 1.8\Omega$ See Fig. 18
t_r	Rise Time	—	19	—		
$t_{d(off)}$	Turn-Off Delay Time	—	18	—		
t_f	Fall Time	—	11	—		
C_{iss}	Input Capacitance	—	4090	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	810	—		
C_{rss}	Reverse Transfer Capacitance	—	390	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	350	mJ
I_{AR}	Avalanche Current ①	—	16	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	170		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 16A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	17	26	ns	$T_J = 25^\circ\text{C}, I_F = 16A, V_{DD} = 15V$
Q_{rr}	Reverse Recovery Charge	—	33	50	nC	$di/dt = 430A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



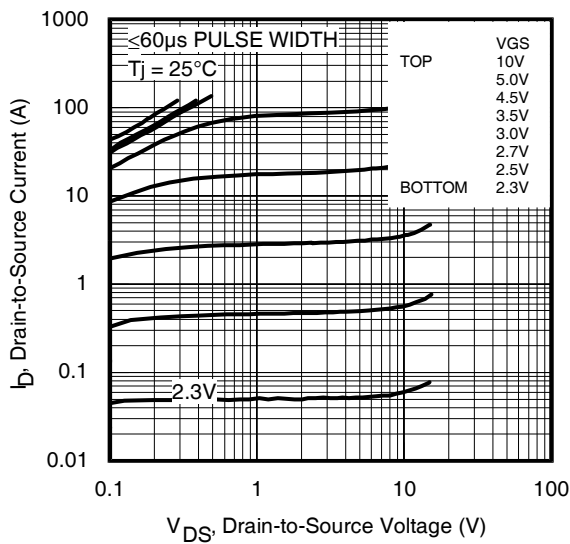


Fig 1. Typical Output Characteristics

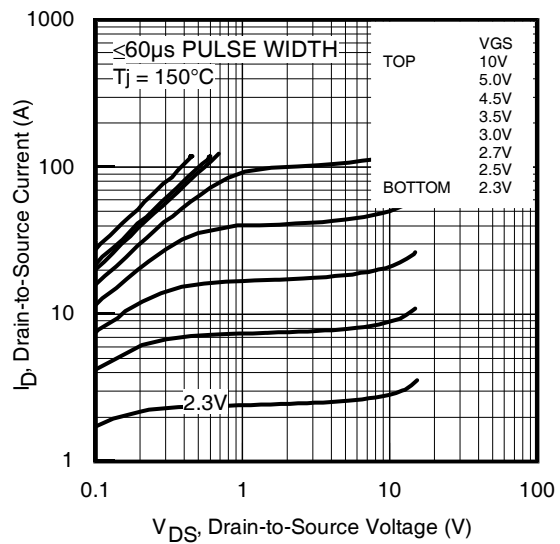


Fig 2. Typical Output Characteristics

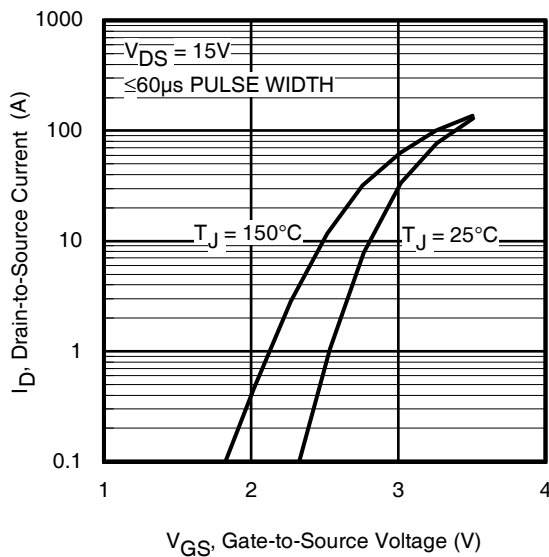


Fig 3. Typical Transfer Characteristics

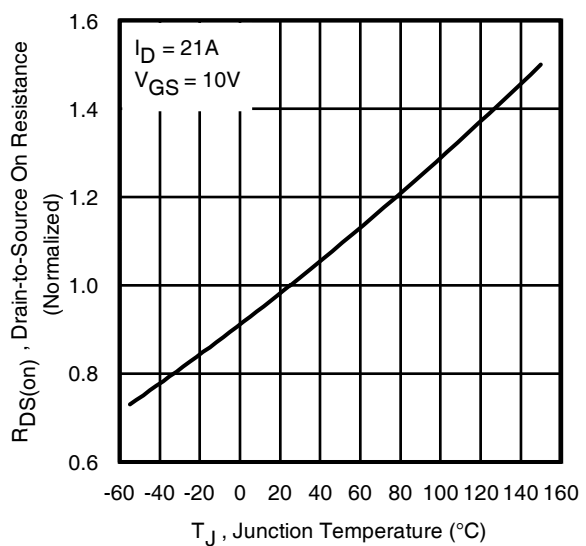


Fig 4. Normalized On-Resistance vs. Temperature

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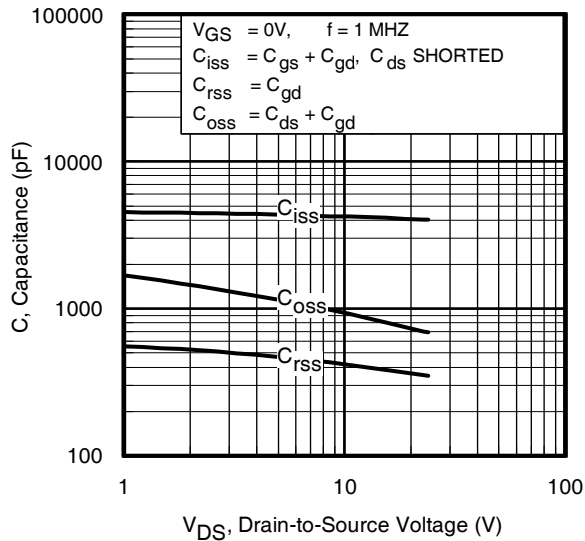


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

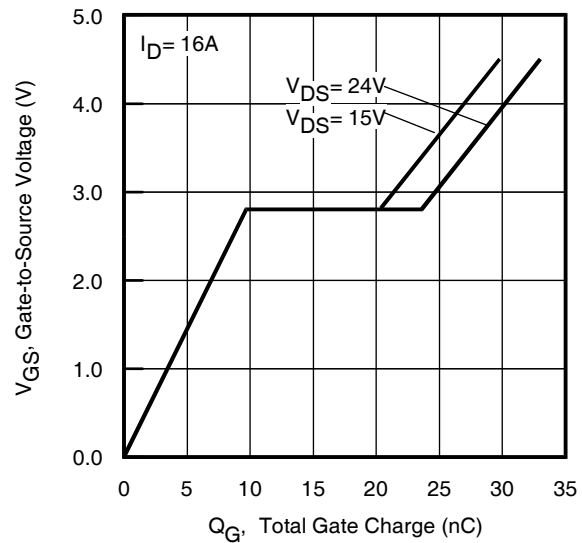


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

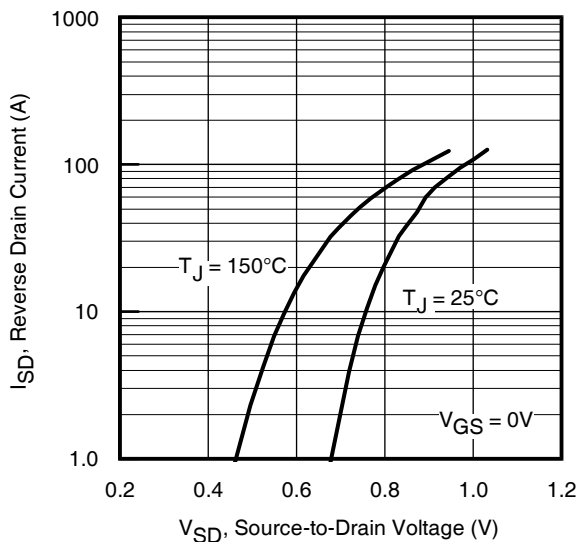


Fig 7. Typical Source-Drain Diode Forward Voltage

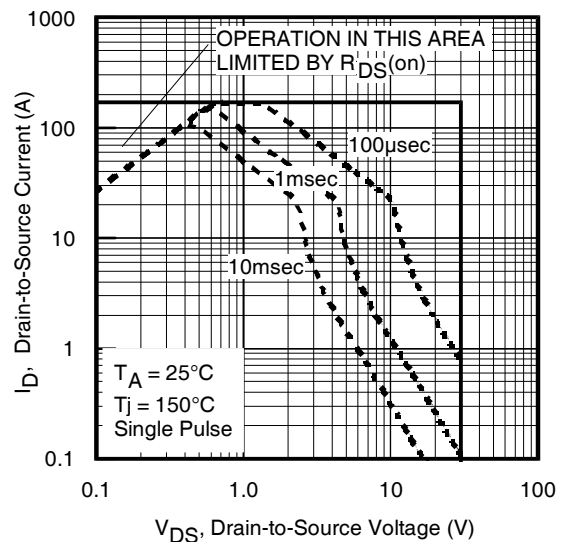


Fig 8. Maximum Safe Operating Area

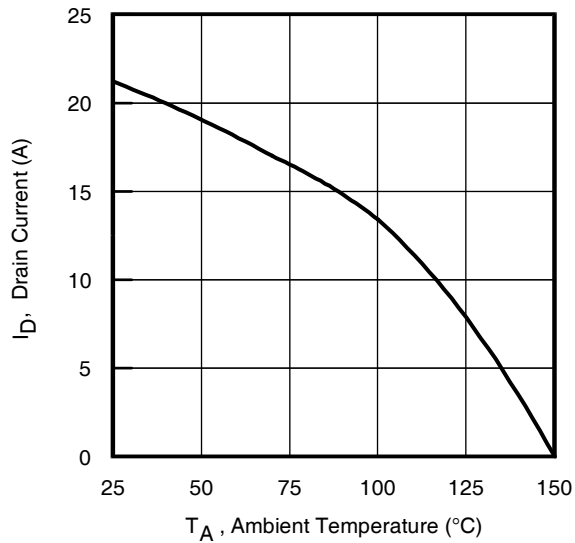


Fig 9. Maximum Drain Current vs. Ambient Temperature

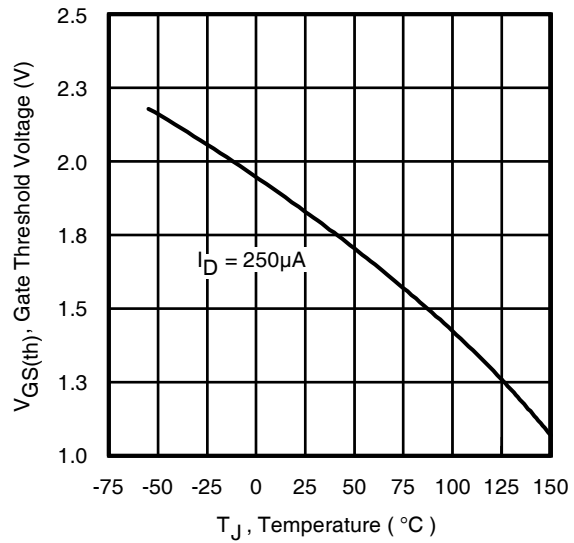


Fig 10. Threshold Voltage vs. Temperature

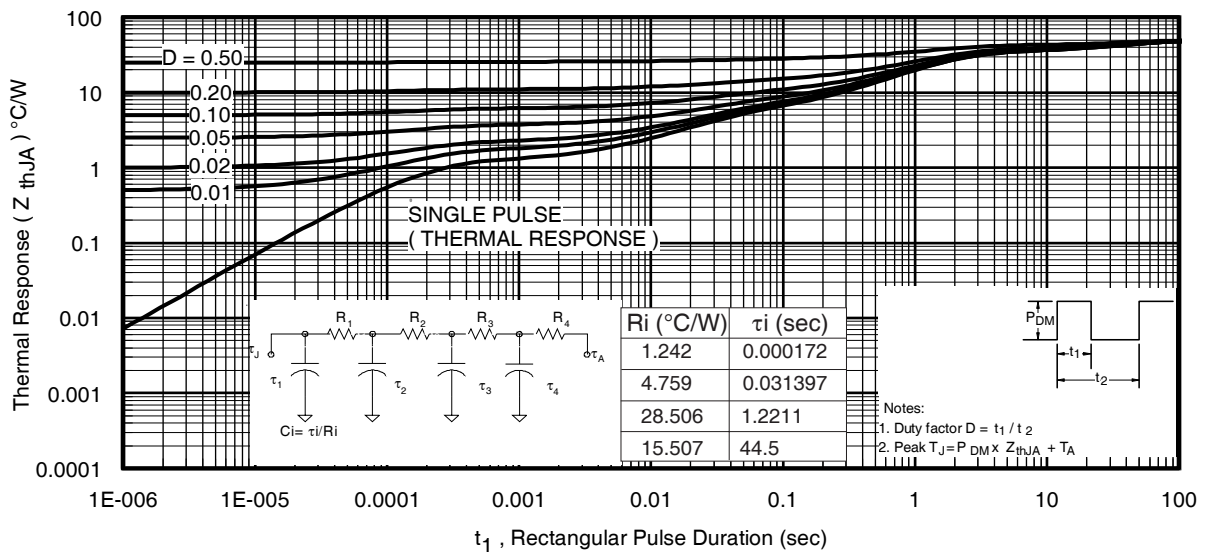


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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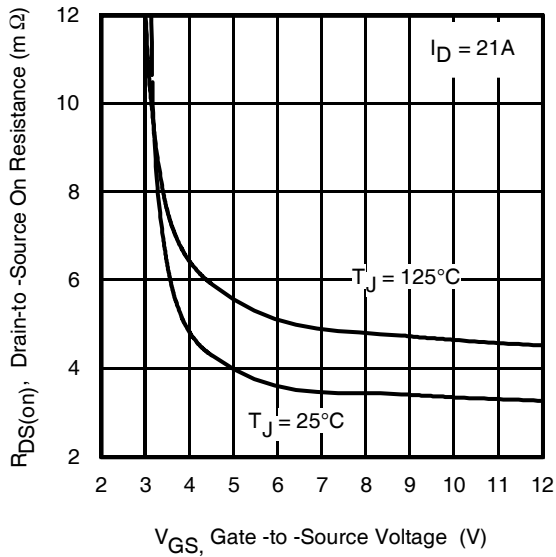


Fig 12. On-Resistance vs. Gate Voltage

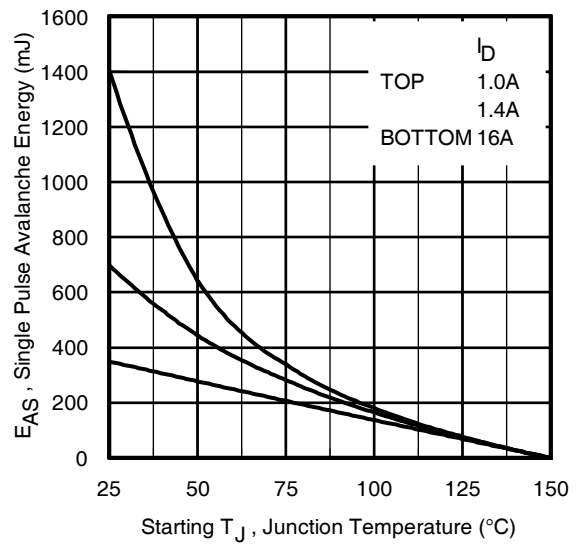


Fig 13. Maximum Avalanche Energy vs. Drain Current

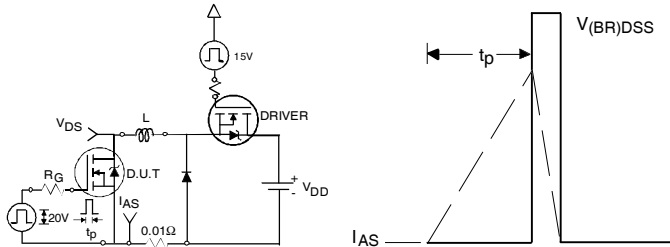


Fig 14. Unclamped Inductive Test Circuit and Waveform

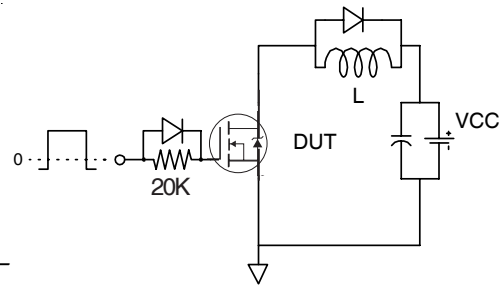


Fig 15. Gate Charge Test Circuit

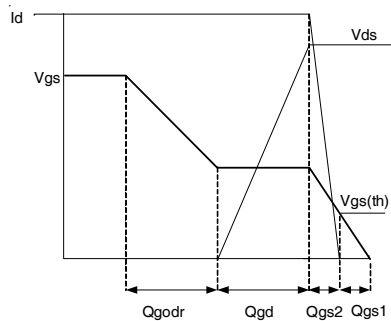


Fig 16. Gate Charge Waveform

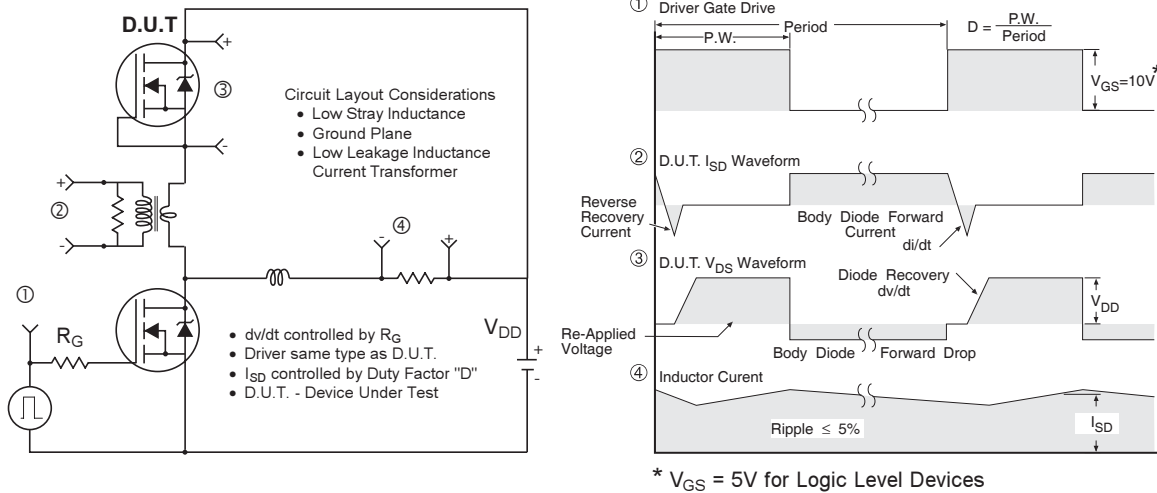


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

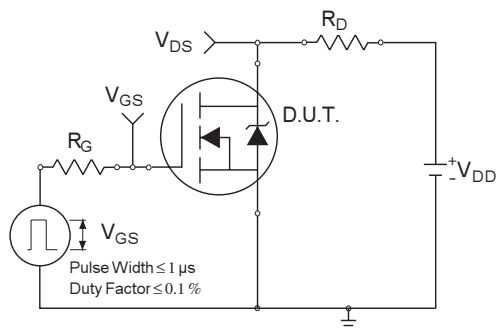


Fig 18a. Switching Time Test Circuit

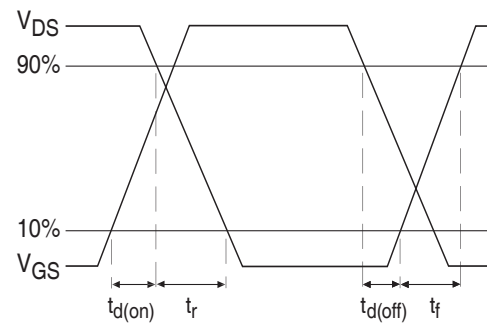


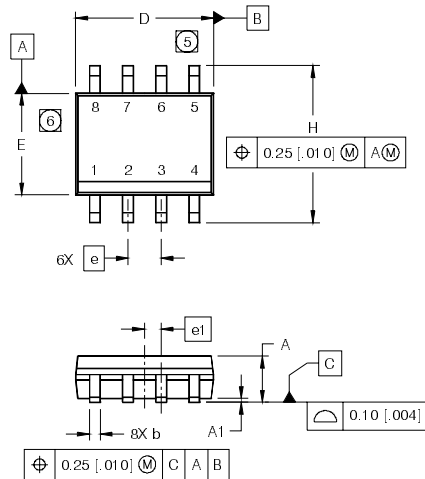
Fig 18b. Switching Time Waveforms

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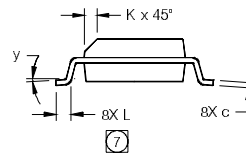
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SO-8 Package Outline(Mosfet & Fetky)

Dimensions are shown in millimeters (inches)



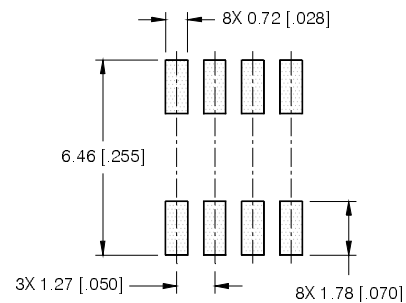
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

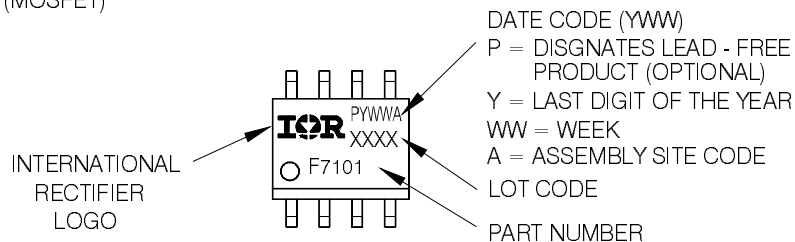
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



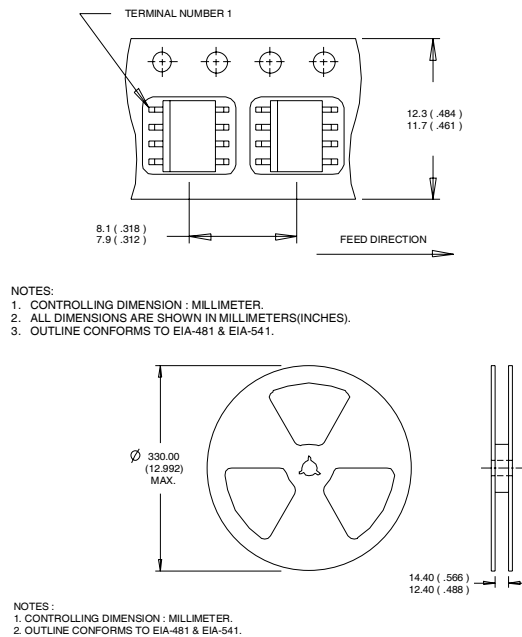
SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SO-8 Tape and Reel Dimensions are shown in millimeters (inches)



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 2.7\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 16\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_{θ} is measured at T_J of approximately 90°C .

Revision History

Date	Comment
6/4/2009	Maximum $R_{ds(on)}$ at $V_{gs} = 10\text{V}$ changed from $3.7\text{m}\Omega$ to $3.3\text{m}\Omega$. All other parameters are unchanged.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.06/2009

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